

Silicon Epitaxial Planar Switching Diode

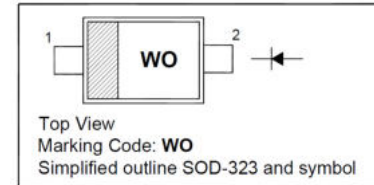


FEATURES:

Fast switching speed
Surface mount package ideally suited for automatic insertion

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



SPECIFICATION:

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Reverse Voltage	V_R	150	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Forward Continuous Current	I_{FM}	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	2.5 0.5	A
Power Dissipation	P_{tot}	200	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	200	-	V
Reverse Current at $V_R = 150\ \text{V}$	I_R	-	100	nA
Forward Voltage at $I_F = 100\ \text{mA}$ at $I_F = 200\ \text{mA}$	V_F	- -	1 1.25	V
Total Capacitance at $V_R = 0, f = 1\ \text{MHz}$	C_T	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\ \text{mA}, I_{RR} = 0.1 \times I_R, R_L = 100\ \Omega$	t_{rr}	-	50	ns

Art. Nr.
RND BAV20WS

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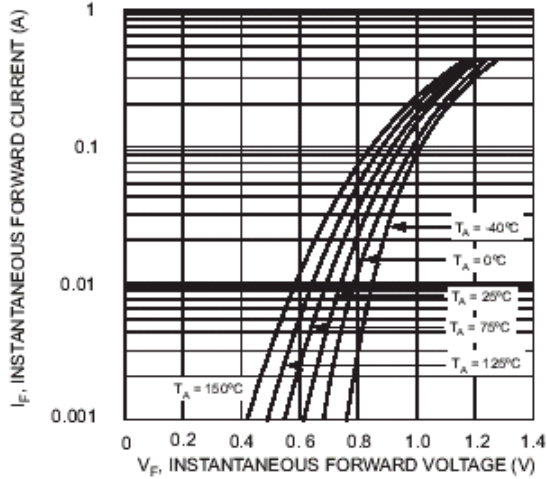


Fig. 1 Typical Forward Characteristics

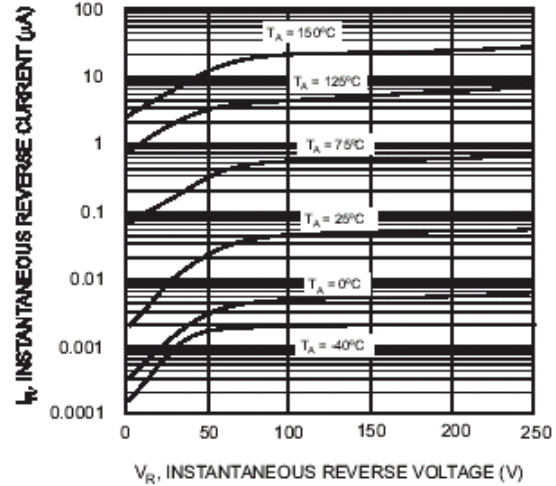


Fig. 2 Typical Reverse Characteristics

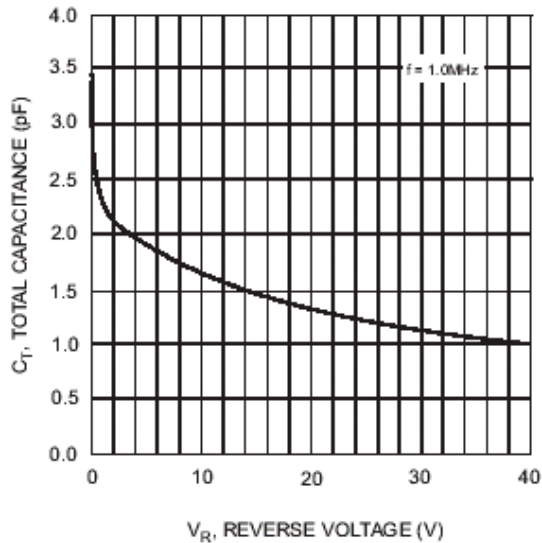


Fig. 3 Typical Capacitance vs. Reverse Voltage

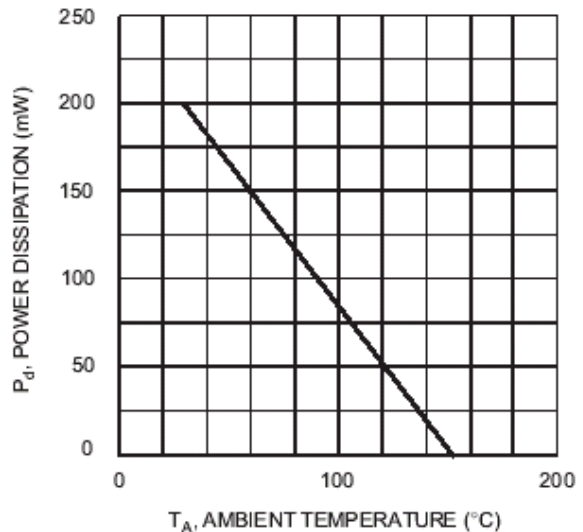


Fig. 4 Power Derating Curve, Total Package